Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group 2812

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A	6,340,628	1/22/02	Van Cleemput, et al.	438	586	12/12/00
	B	6,383,955	5/7/02	Matsuki, et al.	438	790	6/7/99
	C						
	D						
	E						
	F						
	G						
	H						
	I						

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
	J							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	K	Jan, C.H., et al, *90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology*, 2003 IEEE Interconnect Technology Conference.
	L	U.S. Application No. 10/789,103 (Atty Docket No.: NOVLP094), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS, Wu et al.
	M	U.S. Application No. 10/800,409 (Atty Docket No.: NOVLP098), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS, Wu et al.

Examiner Andrew J. Mackowski	Date Considered 09/08/2004

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group ~~2812~~ 2893

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,329,017	12.11.01	Liu et al.	427	240	10/04/99
	A2	6,383,466	05.07.02	Domansky et al.	423	335	12/28/98
	A3	6,365,266	04.02.02	MacDougall et al.	428	304.4	08/03/00
	A4	5,504,042	04.02.96	Cho et al.	438	781	08/23/94
	A5	5,858,457	01.12.96	Brinker et al.	427	162	09/25/97
	A6	6,270,846	08.07.01	Brinker et al.	428	64.1	09/25/00
	A7	6,387,453	05.14.02	Brinker et al.	427	357	03/22/00
	A8	5,789,027	08.04.98	Watkins et al.	427	250	11/12/96
	A9	6,391,932 B1	05.21.02	Gore et al.	521	61	08/28/00
	A10	5,700,844	12.23.97	Hedrick et al.	521	77	08/09/96
	A11	2003/0157248 A1	08.21.03	Watkins et al.	427	256	11/21/02
	A12	2002/0123240 A1	09.05.02	Gallagher et al.	438	781	11/30/01
	A13	6,596,654	07.22.03	Bayman, et al.	438	788	11/28/01
	A14	4,885,262	12.05.89	Ting et al.			
	A15	5,686,054	11.11.97	Barthel et al.			
	A16	5,851,715	12.22.98	Barthel et al.			
	A17	6,140,252	10.31.00	Cho et al.			
	A18	6,392,017	05.21.02	Chandrashekar			
	A19	6,386,466	05.14.02	Ozawa et al.			
	A20	4,357,451	11.02.02	McDaniel			
	A21	6,479,374	11.12.02	Ioka et al.			
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	A23	2004/0099952	05.27.04	Goodner et al.			
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	A29	6,805,801	10.19.04	Humayun et al.			
	A30	6,391,932	05.21.02	Gore et al.			
	A31	6,271,273	10.10.00	You et al.			
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	A33	2002/0034626	03.21.02	Liu et al.			
	A34	2002/0001973	01.03.02	Wu et al.			

Examiner Julian A. Mahdi	Date Considered 09/08/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	A37	6,268,276	07.31.01	Chan et al.			
	A38	6,177,329	01.23.01	Pang			
	A39	5,920,790	07.1999	Wetzel et al.			
	A40	2003/0119307	06.2003	Bekiaris et al.			
	A41	6,596,467	07.22.03	Gallagher et al.			
	A42	6,667,147	12.23.03	Gallagher et al.			
	A43	6,312,793	11.06.01	Grill et al.			
	A44	6,576,345	06.10.03	Cleemput et al.			
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	A49	2003/0064607	04.2003	Leu et al.			
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	A51	6,756,085	06.29.04	Waldfried et al.			

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Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
	B1	WO95/07543	03.16.95	WIPO			X	

Examiner	Date Considered
Julia Q. Haldorado	09/02/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group ~~2812~~ 2823

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	C2	Yung et al., "Spin-on Mesoporous Silica Films with Ultralow Dielectric Constants, Ordered Pore Structures, and Hydrophobic Surfaces," Adv. Mater. 2001, *13*, No. 14, 1099-1102
	C3	Schulberg et al., "System for Deposition of Mesoporous Materials," U.S. Patent Application No. 10/295,965, filed November 15, 2002, 64 Pages
	C4	Watkins et al., "Mesoporous Materials and Methods," U.S. Patent Application No.10/301,013, filed November 21, 2002, 34 Pages
	C5	Justin F. Gaynor, "In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments," U.S. Patent Application No.10/056,926 filed January 24, 2002, 34 Pages
	C6	Humayun et al., "Method for Forming Porous Films By Porogen Removel Combined Wtih In SITU Surface Modification", Novellus Corporation, Application No. 10/404,693, filed 3/31/03, pages 1-32. Atty. Docket No. NOVLP064/NVLS-0007
	C7	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", Novellus Systems, Inc., Application No. 10/672,311, filed 9/26/03, pages 1-27. Atty. Docket No. NOVLP075/NVLS-000820
	C8	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030)
	C9	U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028)
	C10	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1)
	C11	Tipton et al., "Method for Removal of Porogens From Porous Low-K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVLP069/NVLS-000821
	C12	Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002
	C13	Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/800,377, filed 3/11/04, pages 1-31. Atty. Docket No. NOVLP089/NVLS-2887

Examiner	Date Considered
	09/01/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group ~~2812~~ 2823

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	C14	Wu et al., "Method and Apparatus of UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/807,680, filed 3/23/04, pages 1-34. Atty. Docket No. NOVLP097/NVLS-2906
	C15	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064)
	C16	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated September 7, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
	C17	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated December 28, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
	C18	Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Atty Dkt: NOVLP069).
	C19	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure", U.S. Patent Application No. 10/825,888, filed April 16, 2004 (Atty Dkt: NOVLP088US/NVLS-2882)
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	C21	Jin et al., "Nanoporous Silica as an Ultralow-*k* Dielectric," MRS Bulletin, October 1997, Pages 39-42
	C22	Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodocity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572
	C23	Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured AI," Journal of the Electrochemica Society, 148 (4) B152-B156 (2001) Pages B152-B156
	C24	Holland et al., "Nonlithographic Technique for the Production of Large Area High Density Gridded Field Sources," J. Vac. Sci. Technol. B 17(2), Mar/Apr. 1999, Pages 580-582
	C25	Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772
	C26	Clube et al., "White Paper from Holotronic Technologies SA; downloaded from www.hdotronic.com/whitepaper/fine-patt.pdf on March 12, 2002

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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	Application No.:
	NOVLP091	10/820,525
Information Disclosure	Applicant:	
Statement By Applicant	Wu et al.	
	Filing Date	Group
(Use Several Sheets if Necessary)	04-07-2004	2812

Other Documents

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	C30	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003.
	C31	Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), 56 (2003).
	C32	Van Bavel et al., Future Fab International, 16, (2004).
	C33	Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003.
	C34	Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International.
	C35	Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003.
	C36	Bhadri N. Varadarajan, "Tensile Silicon Nitride – P1264 NESL", C & F Study, August 21, 2003.
	C37	Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20,2004, pages 1-24. [Atty Docket No. NOVLP108/NVLS-2933].
	C38	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt: NOVLP099)
	C39	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Office Action dated March 2, 2005, (Atty Dkt: NOVLP099)
	C40	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Final Office Action dated June 13, 2005, (Atty Dkt: NOVLP099)
	C41	Wang et al., "Plasma Detemplating And Silanol Capping Of Porous Dielectric Films", U.S. Application No. 10/785,235, filed February 23, 2004 (Atty Dkt: NOVLP085)
	C42	Varadarajan et al., "Tensile Dielectric Films Using UV Curing", U.S. Application No. 10/972,084, filed October 22, 2004 (Atty Dkt: NOVLP122)
	C43	Fox et al., "Method For Improving Mechanical Properties Of Low Dielectric Constant Materials", U.S. Application No. 10/849,568, filed May 18, 2004 (Atty Dkt: NOVLP083)

Examiner	Date Considered
	09/02/2006

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group 2812

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C44	Fox et al., "Methods For Producing Low-Stress Carbon-Doped Oxide Films With Improved Integration Properties", U.S. Application No. 10/987,208, filed November 12, 2004 (Atty Dkt: NOVLP104)
	C45	Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt: NOVLP100)
	C46	Draeger et al., "Creation Of Porosity In Low-K Films By Photo-Disassociation Of Imbedded Nanoparticles," U.S. Application No. 11/146,456, filed June 6, 2005 (Atty Dkt: NOVLP100X1)
	C47	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 10/927,777, filed August 27, 2004 (Atty Dkt: NOVLP106)
	C48	Wu et al., "Methods For Improving Integration Performance Of Low Stress CDO Films", U.S. Application No. 10/941,502, filed September 14, 2004 (Atty Dkt: NOVLP107)
	C49	Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low-K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115)

Examiner	Date Considered
	09/02/2008

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group ~~2812~~ 2823

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,500,770 B1	12.2002	Cheng et al.	438	782	04/24/02
	A2	2002/0192980 A1	12.2002	Hogle et al.	438	778	04/10/02

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Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed July 13, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].
	C2	U.S. Office Action mailed July 27, 2005, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].

Examiner	Date Considered
	09/02/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group 2812

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed August 24, 2005, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C2	U.S. Office Action mailed September 1, 2005, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].

Examiner	Date Considered
	09/02/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	Application No.:
	NOVLP091	10/820,525
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(Use Several Sheets if Necessary)	04-07-2004	~~2812~~ 2826

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 (Atty Dkt: NOVLP145/NVLS-3106)

Examiner	Date Considered
	09/19/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	Application No.:
Information Disclosure Statement By Applicant	NOVLP091	10/820,525
	Applicant: Wu et al.	
(Use Several Sheets if Necessary)	Filing Date 04-07-2004	Group ~~2812~~ 2823

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Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed December 27, 2005, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919].
	C2	U.S. Office Action mailed December 23, 2005, from U.S Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-002907].
	C3	U.S. Office Action mailed February 7, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].
	C4	U.S. Office Action mailed December 20, 2005, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].
	C5	U.S. Office Action mailed December 20, 2005, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
	C6	U.S. Office Action mailed January 9, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].

Examiner	Date Considered
	09/07/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Atty Docket No.	Application No.:
	NOVLP091	10/820,525
Information Disclosure Statement By Applicant	Applicant: Wu et al.	
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(Use Several Sheets if Necessary)	04-07-2004	~~2812~~ 2823

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	A2	2004/0096586 A1	05.2004	Schulberg et al.	427	372.2	11/13/02
	A3	2003/0198895 A1	10.2003	Toma et al.	430	314	03/04/03
	A4	6,846,380 B2	01.2005	Dickinson et al.	156	345.3	06/13/02

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No

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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
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	C2	U.S. Office Action mailed February 28, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C3	U.S. Office Action mailed March 29, 2006, from U.S Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-002886].

Examiner	Date Considered
Judith Mallinson	07/07/06

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) **Information Disclosure Statement By Applicant** (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525 Group ~~2812~~ 2823

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	A3	6,232,658 B1	05.2001	Catabay et al.	257	701	04/30/99
	A4	6,171,661	01.2001	Zheng et al.	427	535	02/26/01
	A5	2002/0016085	02.2002	Huang et al.	438	778	07/16/01
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	A9	2002/0141024 A1	10.2002	Retschke et al.	359	204	03/03/02
	A10	2002/0064341 A1	05.2002	Fauver et al.	385	25	11/26/01

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932].
	C2	U.S. Office Action mailed May 30, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	C3	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
	C4	U.S. Office Action mailed May 2, 2006, from U.S Application No. 11/050,621 [Atty Dkt No. NOVLP100/NVLS-2956].
	C5	U.S. Office Action mailed June 15, 2006, from U.S Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-2907].
	C6	Kelman et al., "Method for Reducing Stress in Porous Dielectric Films", U.S. Application No. 11/369,311, filed March 6, 2006 (Atty Dkt: NOVLP154/NVLS-3121)
	C7	U.S. Office Action mailed June 28, 2006, from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].
	C8	U.S. Office Action mailed May 2, 2006, from U.S Application No. 10/295,965.
	C9	U.S. Office Action mailed August 9, 2005, from U.S Application No. 10/295,965.
	C10	U.S. Office Action mailed June 14, 2006, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].
Examiner		Date Considered 09/07/2006

Examiner: ~~Initial~~ citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.